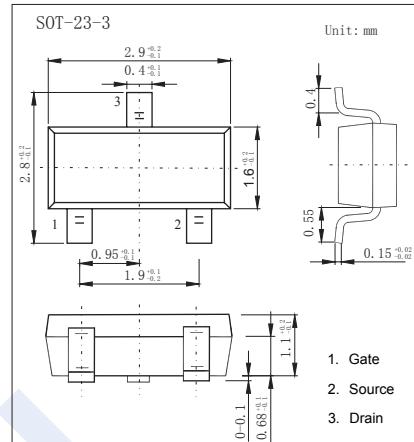
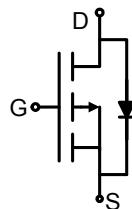


## P-Channel MOSFET

### KI5P04DS

#### ■ Features

- $V_{DS} (V) = -40V$
- $I_D = -5.3 A$  ( $V_{GS} = -10V$ )
- $R_{DS(ON)} < 85m\Omega$  ( $V_{GS} = -10V$ )
- $R_{DS(ON)} < 126m\Omega$  ( $V_{GS} = -4.5V$ )
- High power and current handing capability



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

| Parameter  | Symbol     | Rating     | Unit         |
|--|------------|------------|--------------|
| Drain-Source Voltage                             | $V_{DS}$   | -40        | V            |
| Gate-Source Voltage                              | $V_{GS}$   | $\pm 20$   |              |
| Continuous Drain Current                         | $I_D$      | -5.3       | A            |
| Pulsed Drain Current                             | $I_{DM}$   | -20        |              |
| Power Dissipation                                | $P_D$      | 2          | W            |
| Thermal Resistance.Junction- to-Ambient (Note.1) | $R_{thJA}$ | 62.5       | $^\circ C/W$ |
| Junction Temperature                             | $T_J$      | 150        | $^\circ C$   |
| Junction Storage Temperature Range               | $T_{stg}$  | -55 to 150 |              |

Note.1: Surface Mounted on FR4 Board,  $t \leqslant 10$  sec.

## P-Channel MOSFET

### KI5P04DS

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

| Parameter                             | Symbol              | Test Conditions  | Min | Typ | Max       | Unit             |
|---------------------------------------|---------------------|--|-----|-----|-----------|------------------|
| Drain-Source Breakdown Voltage        | $V_{DSS}$           | $I_D=-250 \mu\text{A}, V_{GS}=0\text{V}$                               | -40 |     |           | V                |
| Zero Gate Voltage Drain Current       | $I_{DSS}$           | $V_{DS}=-40\text{V}, V_{GS}=0\text{V}$                                 |     |     | -1        | $\mu\text{A}$    |
| Gate-Body leakage current             | $I_{GSS}$           | $V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$                              |     |     | $\pm 100$ | nA               |
| Gate Threshold Voltage                | $V_{GS(\text{th})}$ | $V_{DS}=V_{GS}, I_D=-250 \mu\text{A}$ (Note.1)                         | -1  |     | -3        | V                |
| Static Drain-Source On-Resistance     | $R_{DS(\text{on})}$ | $V_{GS}=-10\text{V}, I_D=-5\text{A}$ (Note.1)                          |     | 85  |           | $\text{m}\Omega$ |
|                                       |                     | $V_{GS}=-4.5\text{V}, I_D=-4\text{A}$ (Note.1)                         |     | 126 |           |                  |
| Forward Transconductance              | $g_{FS}$            | $V_{DS}=-5\text{V}, I_D=-4.1\text{A}$                                  | 10  |     |           | S                |
| Input Capacitance                     | $C_{iss}$           | $V_{GS}=0\text{V}, V_{DS}=-20\text{V}, f=1\text{MHz}$                  |     | 650 |           | $\text{pF}$      |
| Output Capacitance                    | $C_{oss}$           |  |     | 90  |           |                  |
| Reverse Transfer Capacitance          | $C_{rss}$           |  |     | 70  |           |                  |
| Total Gate Charge                     | $Q_g$               | $V_{GS}=-10\text{V}, V_{DS}=-20\text{V}, I_D=-3.1\text{A}$             |     | 14  |           | $\text{nC}$      |
| Gate Source Charge                    | $Q_{gs}$            |  |     | 2.9 |           |                  |
| Gate Drain Charge                     | $Q_{gd}$            |  |     | 3.8 |           |                  |
| Turn-On Delay Time                    | $t_{d(on)}$         | $V_{GS}=-10\text{V}, V_{DS}=-20\text{V}, R_L=2\Omega, R_{GEN}=3\Omega$ |     | 9   |           | $\text{ns}$      |
| Turn-On Rise Time                     | $t_r$               |  |     | 8   |           |                  |
| Turn-Off Delay Time                   | $t_{d(off)}$        |  |     | 28  |           |                  |
| Turn-Off Fall Time                    | $t_f$               |  |     | 10  |           |                  |
| Maximum Body-Diode Continuous Current | $I_S$               |  |     |     | -5.3      | A                |
| Diode Forward Voltage                 | $V_{SD}$            | $I_S=-2.5\text{A}, V_{GS}=0\text{V}$ (Note.1)                          |     |     | -1.2      | V                |

Note.1: Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2$ .

■ Marking

|         |       |
|---------|-------|
| Marking | 40P05 |
|---------|-------|